ABSTRACT

WAFERLESS AUTO CONDITIONING

A method for reducing contamination in an etch chamber is provided. A substrate with a metal containing layer is placed in the etch chamber. The metal containing layer is etched, producing nonvolatile metal residue deposits on surfaces of the etch chamber, wherein some of the metal residue of the metal residue deposits is in a first state. The substrate is removed from the etch chamber. The chamber is conditioned by converting metal residue in the first state to metal residue in a second state, where metal residue in the second state has stronger adhesion to surfaces of the etch chamber than metal residue in the first state.

FIG. 1

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